

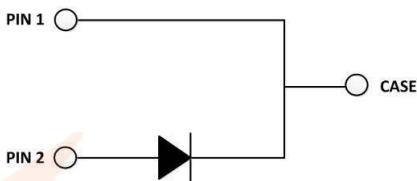
3rd Generation 1200V/50A SiC Schottky Barrier Diode

Features

- Revolutionary semiconductor material - Silicon Carbide (SiC)
- No reverse recovery
- High-speed switching performance
- Temperature-independent switching behavior
- System cost / size savings due to reduced cooling requirements
- Junction temperature range from -55°C to 175°C
- RoHS compliant

Potential Applications

- Industrial power supplies: Industrial UPS
- Battery chargers
- Solar inverters
- Switch mode power supplies



Package Type: TO-247-2L



Description

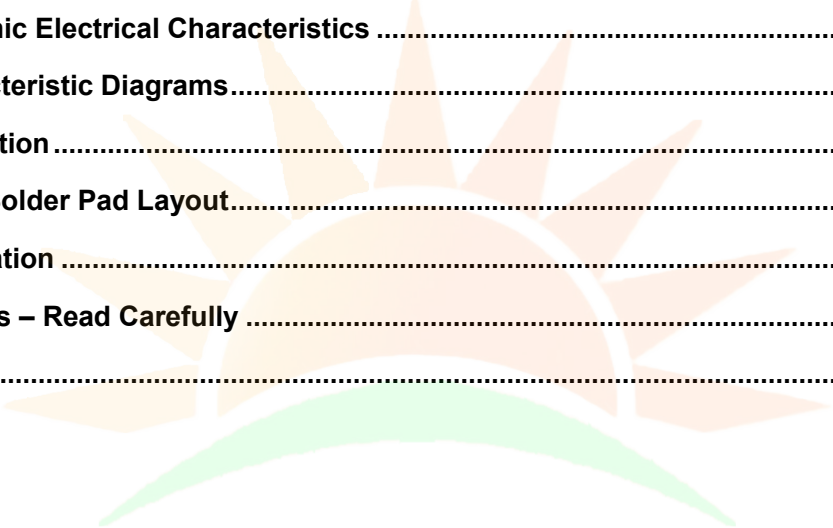
TheHDS120J050H3 SiC Schottky Barrier Diode (SBD) has been developed using Huashentai's advanced 3rd generation SiC SBD technology with the highest performance and reliability. It registers higher efficiency, higher operation temperature and lower loss and can be operated at higher frequency than Si-based solutions. As to the Schottky structure, it shows no recovery at turn-off and allows a low leakage current with reverse voltage up to 1200V. It can contribute to system miniaturization and achieve lightweight system design. Using RoHS compliant components, it is qualified for use in industrial application.

Product Specifications

Device	V _{RRM}	I _F (135°C)	V _F (25°C)	Q _c	Marking
HDS120J050H3	1200V	68A	1.35V	304nC	DS120050H3

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ASMTc

Table 1. Maximum Ratings

(T_c = 25°C, unless otherwise specified)

Parameter	Symbol	Value	Unit	Test conditions
Repetitive peak reverse voltage	V _{RRM}	1200	V	T _C = 25°C
Surge peak reverse voltage	V _{RSM}	1200		T _C = 25°C
DC reverse voltage	V _{DC}	1200		T _C = 25°C
Continuous forward current	I _F	145	A	T _C = 25°C
		68		T _C = 135°C
		50		T _C = 153°C
Surge non-repetitive forward current	I _{FSM}	504	A	T _C = 25°C, t _p = 10ms, half sine pulse
Surge repetitive forward current	I _{FRM}	202	A	T _C = 25°C, t _p = 10ms, half sine wave D = 0.1
Power dissipation	P _{tot}	555	W	T _C = 25°C
i ² t value	∫i ² dt	1270	A ² s	T _C = 25°C, t _p = 10ms
Operating junction temperature	T _j	-55~175	°C	
Storage temperature	T _{stg}	-55~175	°C	
Mounting torque	M	1	Nm	M3 screw

Table 2. Thermal Resistance

Parameter	Symbol	Values			Unit	Test condition
		Min.	Typ.	Max.		
Thermal resistance from junction to case	R _{th(j-c)}	/	0.27	/	°C/W	

Table 3. Static Electrical Characteristics

($T_j = 25^\circ\text{C}$, unless otherwise specified)

Parameter	Symbol	Values			Unit	Test conditions
		Min.	Typ.	Max.		
DC blocking voltage	V_{DC}	1200	/	/	V	$I_R = 200\ \mu\text{A}$
Forward voltage	V_F	/	1.35	1.50	V	$I_F = 50\text{A}$, $T_j = 25^\circ\text{C}$
		/	1.75	2.20		$I_F = 50\text{A}$, $T_j = 175^\circ\text{C}$
Reverse current	I_R	/	5	120	μA	$V_R = 1200\text{V}$, $T_j = 25^\circ\text{C}$
		/	40	800		$V_R = 1200\text{V}$, $T_j = 175^\circ\text{C}$

Table 4. Dynamic Electrical Characteristics

($T_j = 25^\circ\text{C}$, unless otherwise specified)

Parameter	Symbol	Values			Unit	Test conditions
		Min.	Typ.	Max.		
Total capacitance	C	/	4547	/	pF	$V_R = 0\text{V}$, $f = 1\text{MHz}$
		/	285	/		$V_R = 400\text{V}$, $f = 1\text{MHz}$
		/	202	/		$V_R = 800\text{V}$, $f = 1\text{MHz}$
Total capacitive charge	Q_C	/	304	/	nC	$V_R = 800\text{V}$
Capacitance stored energy	E_C	/	86	/	μJ	$V_R = 800\text{V}$

Electrical Characteristic Diagrams

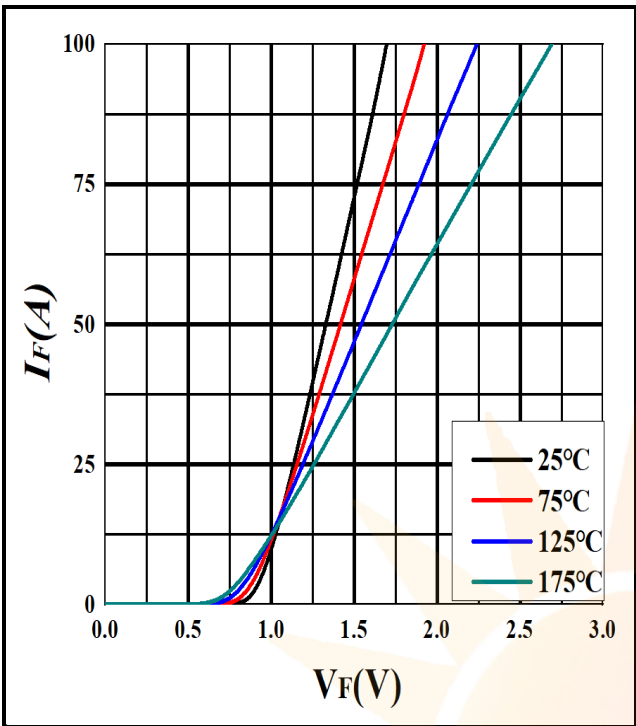


Figure 1. Forward characteristics

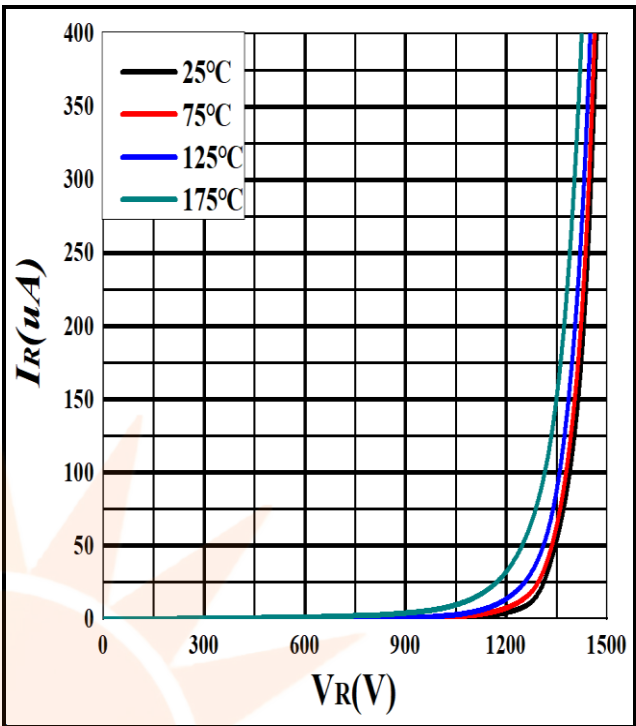


Figure 2. Reverse characteristics

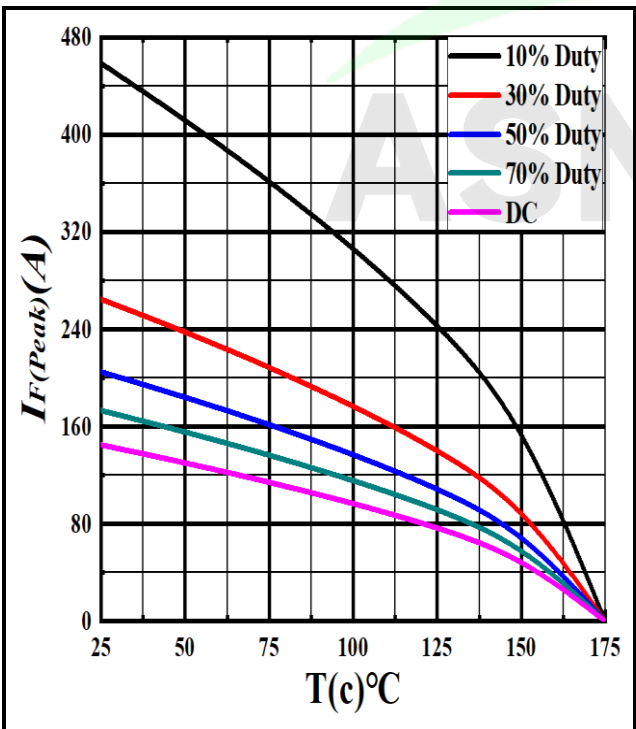


Figure 3. Current derating

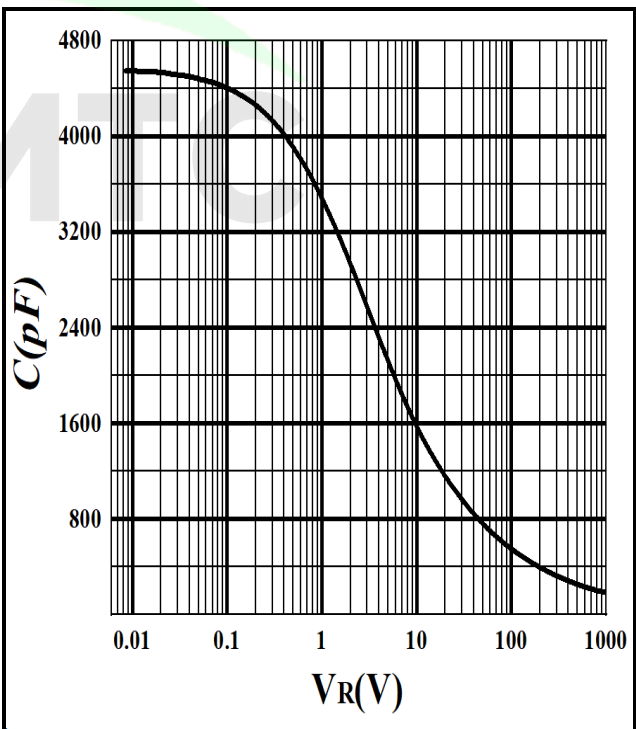


Figure 4. Capacitance vs. reverse voltage

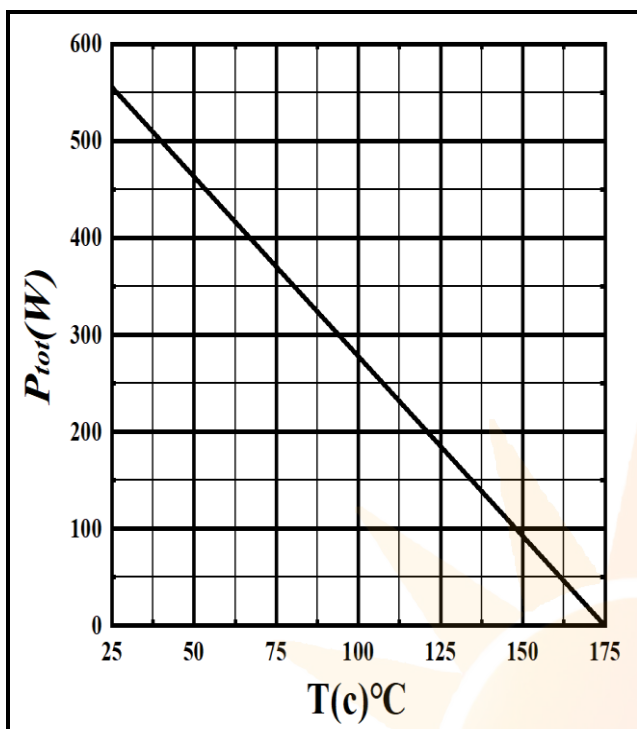


Figure 5. Power derating

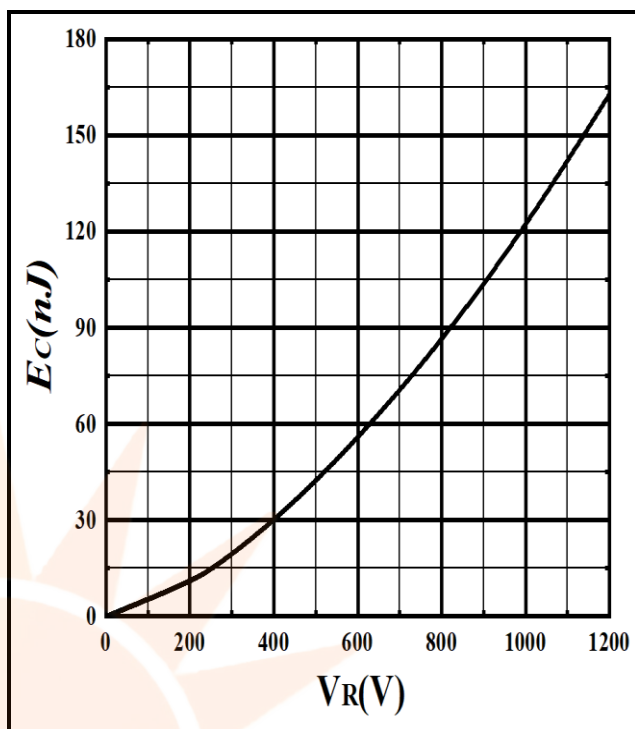


Figure 6. Capacitance stored energy

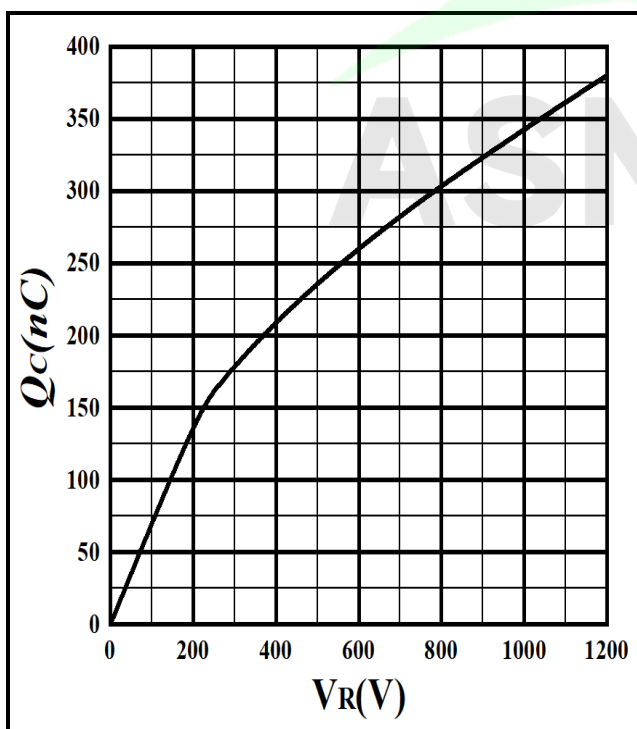
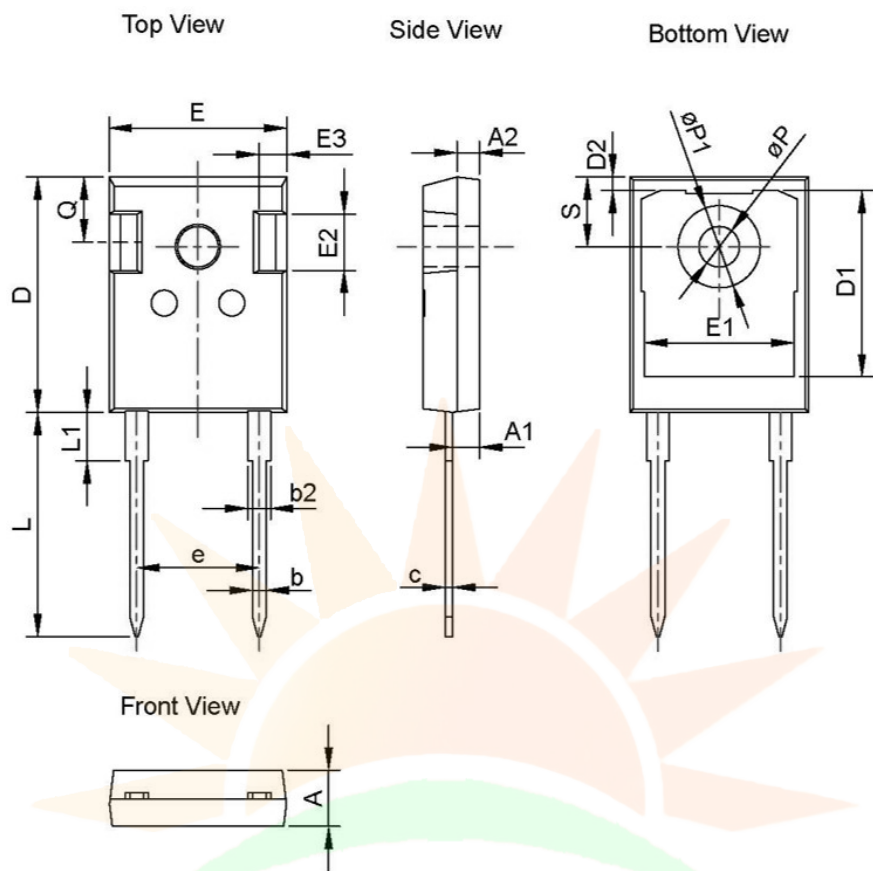


Figure 7. Total capacitance charge vs. reverse voltage

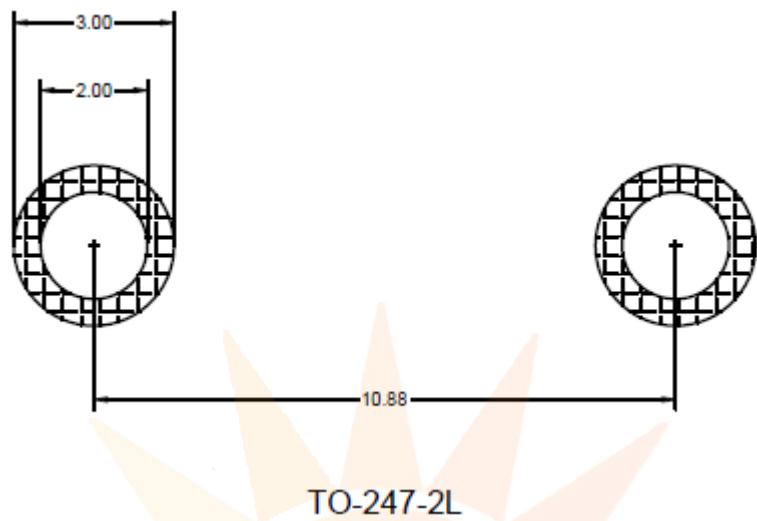
Package Information



Dimension unit: [mm]			
Symbol	Min	Nom	Max
A	4.80	5.00	5.20
A1	2.21	2.41	2.61
A2	1.85	2.00	2.15
b	1.11	1.21	1.36
b2	1.91	2.01	2.21
c	0.51	0.60	0.75
D	20.70	21.00	21.30
D1	16.25	16.55	16.85
D2	1.00	1.20	1.35
E	15.50	15.80	16.10
E1	13.00	13.30	13.60
E2	4.80	5.00	5.20
E3	2.30	2.50	2.70
e	10.88 BSC		
L	19.62	19.92	20.22
L1	-	-	4.30
ϕP	3.40	3.60	3.80
$\phi P1$	-	-	7.30
Q	5.40	5.80	6.20
S	6.20 BSC		

Recommended Solder Pad Layout

Note: All dimensions are in mm



Ordering Information

Part number	HDS120J050H3-ISATH
Package	TO-247-2L
Unit quantity	300 EA
Packing type	Tube

Important Notices – Read Carefully

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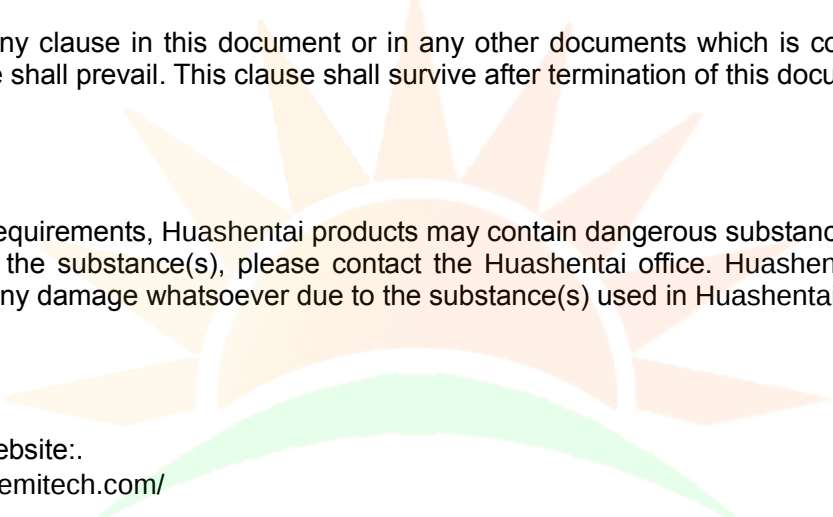
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Warning

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